

BUK7608-40B

N-channel TrenchMOS standard level FET

Rev. 04 — 24 September 2008

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

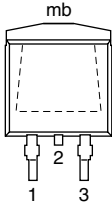
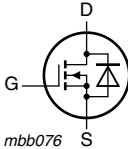
Table 1. Quick reference

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|--|---|-----|-----|-----|------------|
| V_{DS} | drain-source voltage | $T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$ | - | - | 40 | V |
| I_D | drain current | $V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C};$ see Figure 1 ; see Figure 3 ; | [1] | - | 75 | A |
| P_{tot} | total power dissipation | $T_{mb} = 25\text{ °C};$ see Figure 2 | - | - | 157 | W |
| Avalanche ruggedness | | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $I_D = 75\text{ A}; V_{sup} \leq 40\text{ V};$ $R_{GS} = 50\text{ }\Omega; V_{GS} = 10\text{ V};$ $T_{j(init)} = 25\text{ °C};$ unclamped | - | - | 241 | mJ |
| Dynamic characteristics | | | | | | |
| Q_{GD} | gate-drain charge | $V_{GS} = 10\text{ V}; I_D = 25\text{ A};$ $V_{DS} = 32\text{ V}; T_j = 25\text{ °C};$ see Figure 14 | - | 12 | - | nC |
| Static characteristics | | | | | | |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = 10\text{ V}; I_D = 25\text{ A};$ $T_j = 25\text{ °C};$ see Figure 12 ; see Figure 11 | - | 6.6 | 8 | m Ω |

[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|---|---|
| 1 | G | gate |  <p>SOT404 (D2PAK)</p> |  <p>mbb076</p> |
| 2 | D | drain [1] | | |
| 3 | S | source | | |
| mb | D | mounting base; connected to drain | | |

[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3. Ordering information

| Type number | Package | | Version |
|-------------|---------|--|---------|
| | Name | Description | |
| BUK7608-40B | D2PAK | Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404 |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------------|-------------------------|--|-----|-----|------|
| V_{DS} | drain-source voltage | $T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$ | - | 40 | V |
| V_{DGR} | drain-gate voltage | $R_{GS} = 20\text{ k}\Omega$ | - | 40 | V |
| V_{GS} | gate-source voltage | | -20 | 20 | V |
| I_D | drain current | $T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1 ; see Figure 3 ; [1] | - | 101 | A |
| | | $T_{mb} = 100\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1 ; [1] | - | 71 | A |
| | | $T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1 ; see Figure 3 ; [2] | - | 75 | A |
| I_{DM} | peak drain current | $T_{mb} = 25\text{ °C}$; $t_p \leq 10\text{ }\mu\text{s}$; pulsed; see Figure 3 | - | 407 | A |
| P_{tot} | total power dissipation | $T_{mb} = 25\text{ °C}$; see Figure 2 | - | 157 | W |
| T_{stg} | storage temperature | | -55 | 175 | °C |
| T_j | junction temperature | | -55 | 175 | °C |
| Source-drain diode | | | | | |
| I_S | source current | $T_{mb} = 25\text{ °C}$; [1] | - | 101 | A |
| | | $T_{mb} = 25\text{ °C}$; [2] | - | 75 | A |
| I_{SM} | peak source current | $t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$ | - | 407 | A |

Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------------------------|--|---|-----|-----|------|
| Avalanche ruggedness | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $I_D = 75\text{ A}$; $V_{sup} \leq 40\text{ V}$; $R_{GS} = 50\ \Omega$; $V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; unclamped | - | 241 | mJ |

- [1] Current is limited by power dissipation chip rating.
- [2] Continuous current is limited by package.

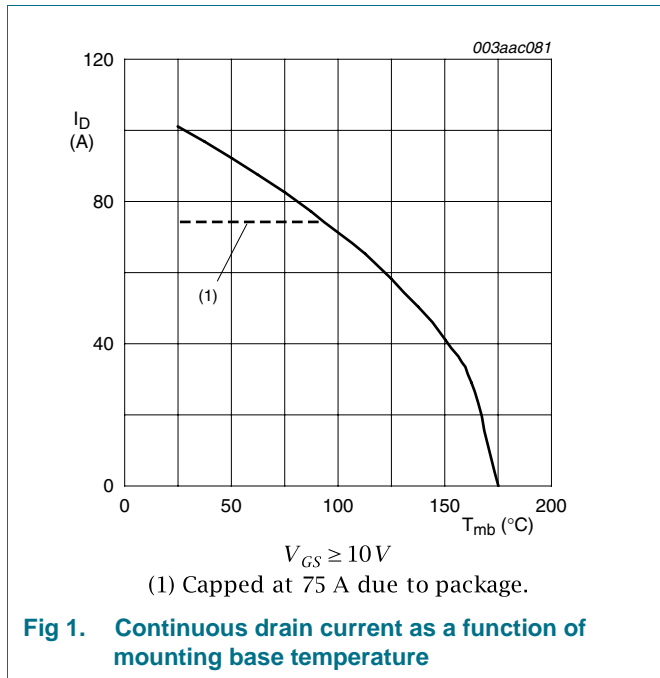


Fig 1. Continuous drain current as a function of mounting base temperature

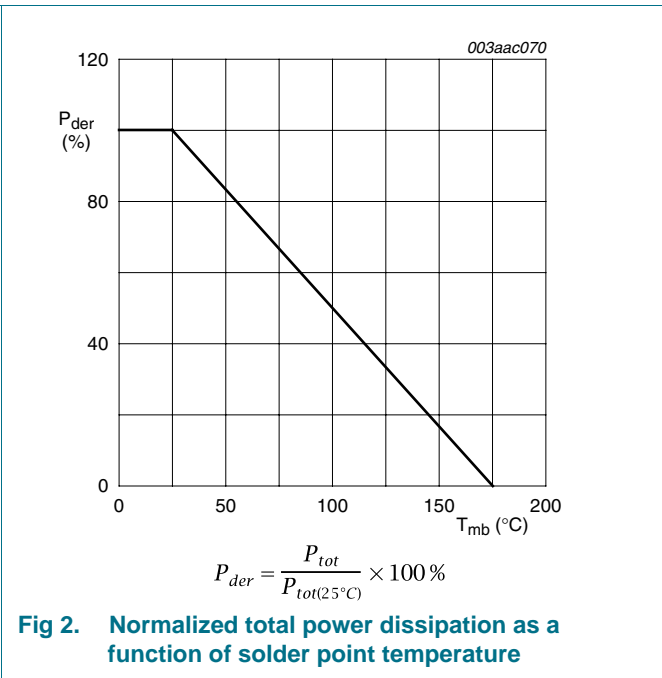


Fig 2. Normalized total power dissipation as a function of solder point temperature

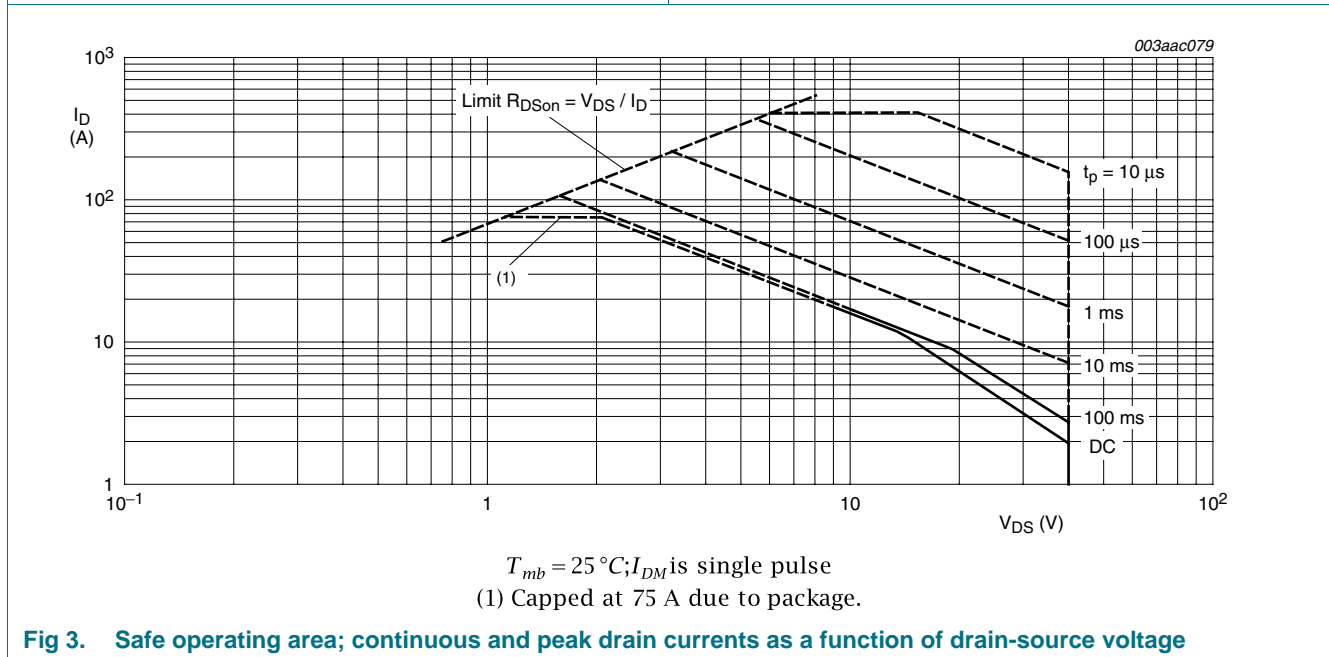


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|---|---|-----|-----|------|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | mounted on a printed-circuit board; minimum footprint | - | 50 | - | K/W |
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see Figure 4 | - | - | 0.95 | K/W |

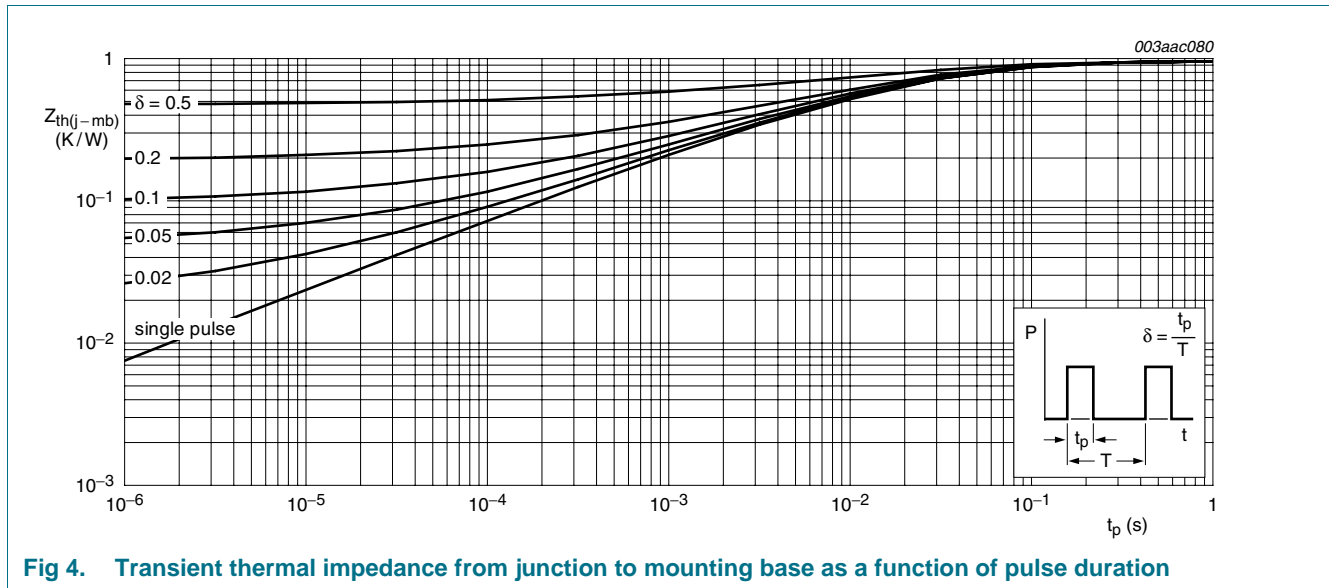
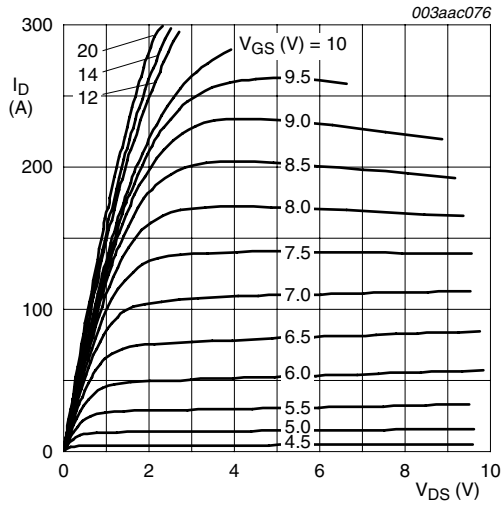


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

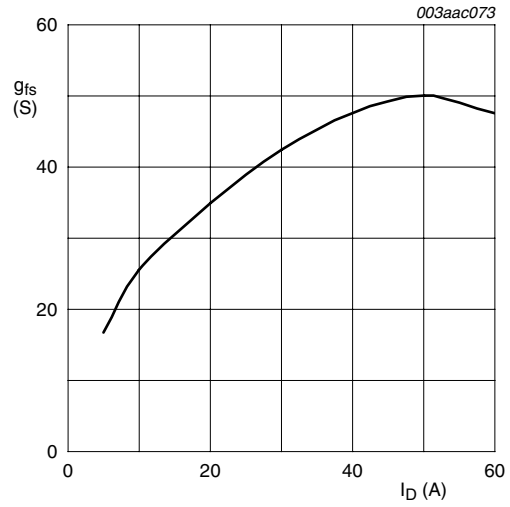
Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|----------------------------------|---|-----|------|------|---------------|
| Static characteristics | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | 40 | - | - | V |
| | | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$ | 36 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C}$; see Figure 9 ; see Figure 10 | 2 | 3 | 4 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C}$; see Figure 9 ; see Figure 10 | - | - | 4.4 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C}$; see Figure 9 ; see Figure 10 | 1 | - | - | V |
| I_{DSS} | drain leakage current | $V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | 0.02 | 1 | μA |
| | | $V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$ | - | - | 500 | μA |
| I_{GSS} | gate leakage current | $V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | 2 | 100 | nA |
| | | $V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | 2 | 100 | nA |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C}$; see Figure 11 ; see Figure 12 | - | - | 15.2 | m Ω |
| | | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$; see Figure 12 ; see Figure 11 | - | 6.6 | 8 | m Ω |
| Dynamic characteristics | | | | | | |
| $Q_{G(tot)}$ | total gate charge | $I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$; see Figure 14 | - | 36 | - | nC |
| Q_{GS} | gate-source charge | | - | 9 | - | nC |
| Q_{GD} | gate-drain charge | | - | 12 | - | nC |
| C_{iss} | input capacitance | $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C}$; see Figure 15 | - | 2017 | 2689 | pF |
| C_{oss} | output capacitance | | - | 486 | 583 | pF |
| C_{rss} | reverse transfer capacitance | | - | 213 | 291 | pF |
| $t_{d(on)}$ | turn-on delay time | $V_{DS} = 30 \text{ V}; R_L = 1.2 \text{ } \Omega; V_{GS} = 10 \text{ V}; R_{G(ext)} = 10 \text{ } \Omega; T_j = 25 \text{ }^\circ\text{C}$ | - | 20 | - | ns |
| t_r | rise time | | - | 51 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 20 | - | ns |
| t_f | fall time | | - | 33 | - | ns |
| L_D | internal drain inductance | from drain lead 6 mm from package to center of die; $T_j = 25 \text{ }^\circ\text{C}$ | - | 4.5 | - | nH |
| | | from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ }^\circ\text{C}$ | - | 2.5 | - | nH |
| L_S | internal source inductance | from source lead 6 mm from package to source bond pad; $T_j = 25 \text{ }^\circ\text{C}$ | - | 7.5 | - | nH |
| Source-drain diode | | | | | | |
| V_{SD} | source-drain voltage | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$; see Figure 13 | - | 0.85 | 1.2 | V |
| t_{rr} | reverse recovery time | $I_S = 20 \text{ A}; di_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = -10 \text{ V}; V_{DS} = 20 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | 53 | - | ns |
| Q_r | recovered charge | | - | 44 | - | nC |



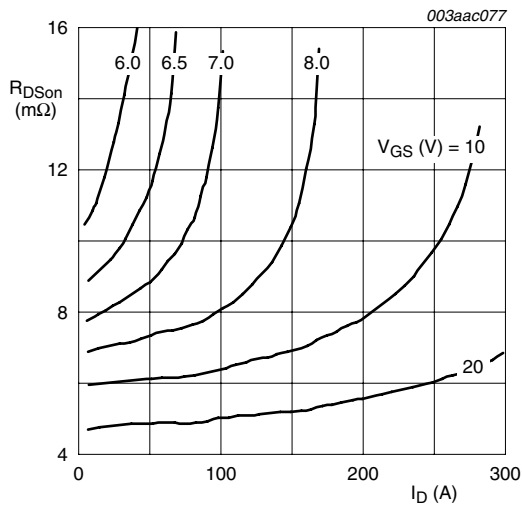
$T_j = 25^\circ\text{C}; t_p = 300\mu\text{s}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



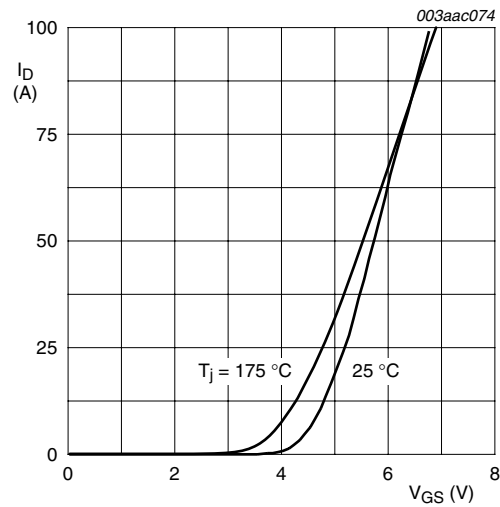
$T_j = 25^\circ\text{C}; V_{DS} = 25\text{V}$

Fig 6. Forward transconductance as a function of drain current; typical values



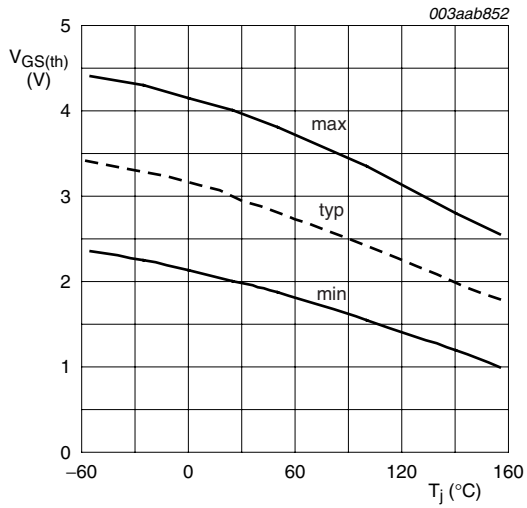
$T_j = 25^\circ\text{C}$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values



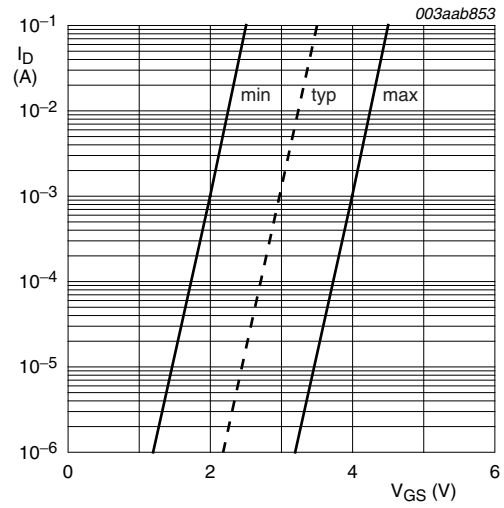
$V_{DS} = 25\text{V}$

Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values



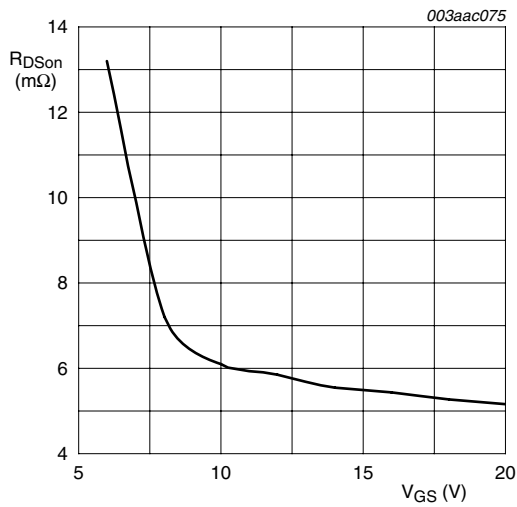
$$I_D = 1\text{ mA}; V_{DS} = V_{GS}$$

Fig 9. Gate-source threshold voltage as a function of junction temperature



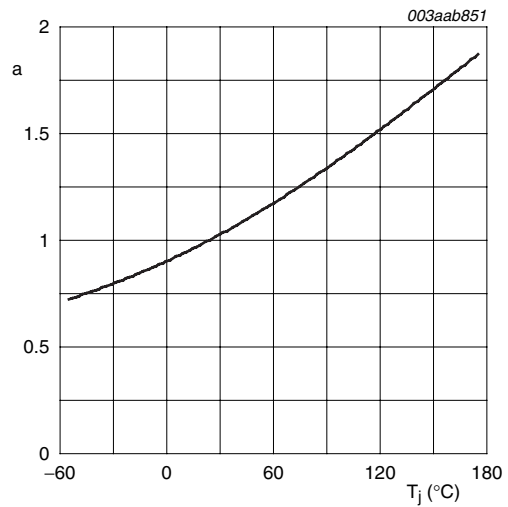
$$T_j = 25\text{ }^\circ\text{C}; V_{DS} = V_{GS}$$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



$$T_j = 25\text{ }^\circ\text{C}; I_D = 25\text{ A}$$

Fig 11. Drain-source on-state resistance as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

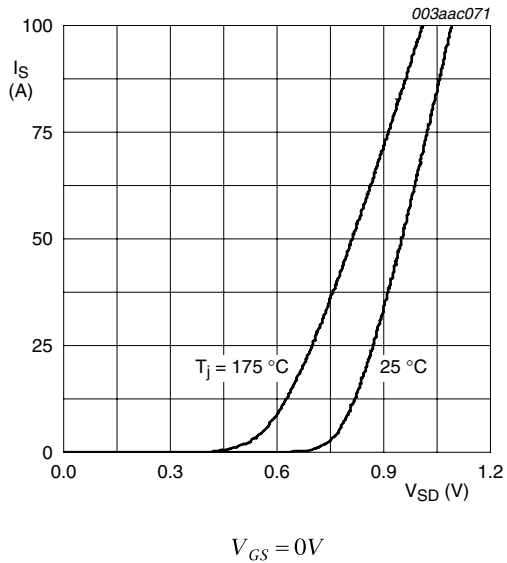


Fig 13. Reverse diode current as a function of reverse diode voltage; typical values

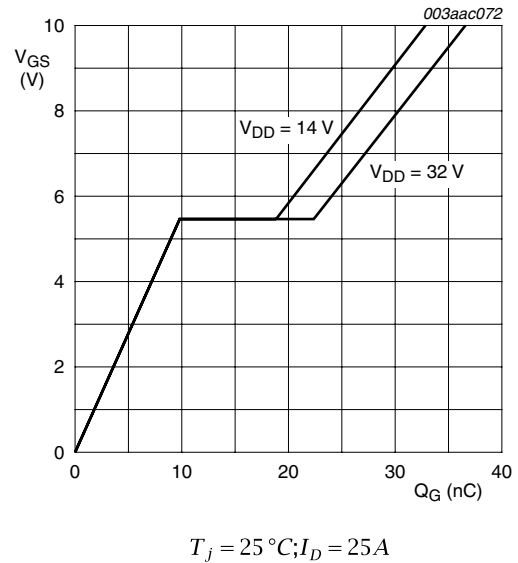


Fig 14. Gate-source voltage as a function of turn-on gate charge; typical values

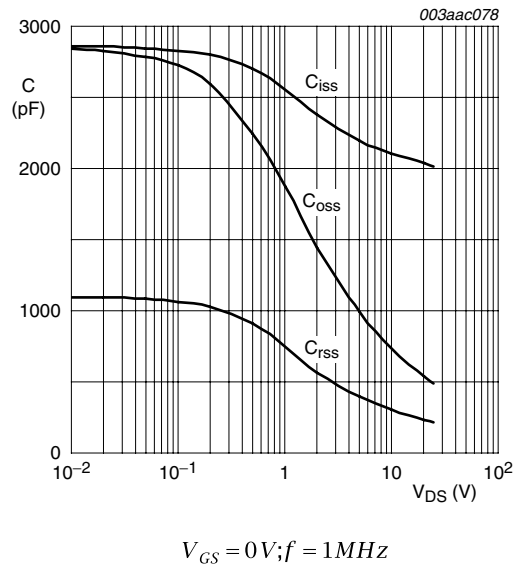
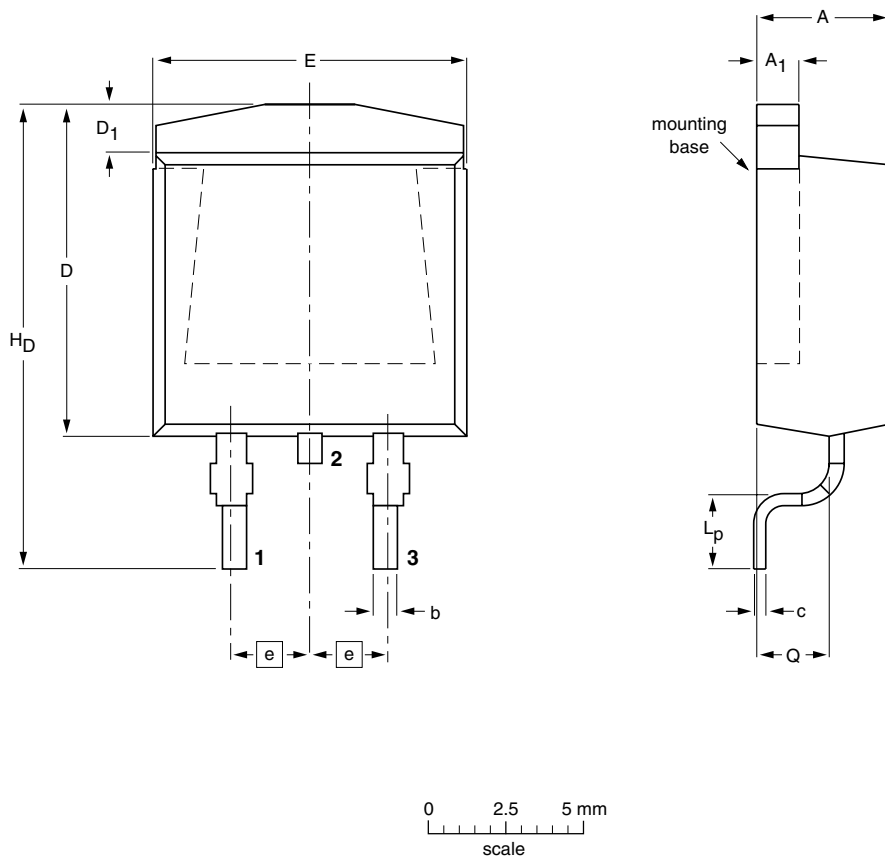


Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

SOT404



DIMENSIONS (mm are the original dimensions)

| UNIT | A | A ₁ | b | c | D max. | D ₁ | E | e | L _p | H _D | Q |
|------|------|----------------|------|------|-----------|----------------|-------|------|----------------|----------------|------|
| mm | 4.50 | 1.40 | 0.85 | 0.64 | 11 | 1.60 | 10.30 | 2.54 | 2.90 | 15.80 | 2.60 |
| | 4.10 | 1.27 | 0.60 | 0.46 | | 1.20 | 9.70 | | | | |

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|-------|-------|--|---------------------|----------------------|
| | IEC | JEDEC | JEITA | | | |
| SOT404 | | | | | | 05-02-11 06-03-16 |

Fig 16. Package outline SOT404 (D2PAK)

8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-------------------|--|--------------------|---------------|-------------------|
| BUK7608-40B_4 | 20080924 | Product data sheet | - | BUK75_7608-40B_3 |
| Modifications: | • Type number BUK7608-40B separated from data sheet BUK75_7608-40B_3 | | | |
| BUK75_7608-40B_3 | 20071128 | Product data sheet | - | BUK75_7608-40B_2 |
| BUK75_7608-40B_2 | 20071116 | Product data sheet | - | BUK75_7608_40B-01 |
| BUK75_7608_40B-01 | 20030319 | Product data sheet | - | - |

9. Legal information

9.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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